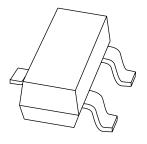
## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



BC846; BC847; BC848 NPN general purpose transistors

Product specification Supersedes data of 2002 Feb 04 2004 Feb 06





## **NPN** general purpose transistors

BC846; BC847; BC848

#### **FEATURES**

• Low current (max. 100 mA)

• Low voltage (max. 65 V).

#### **APPLICATIONS**

• General purpose switching and amplification.

#### **DESCRIPTION**

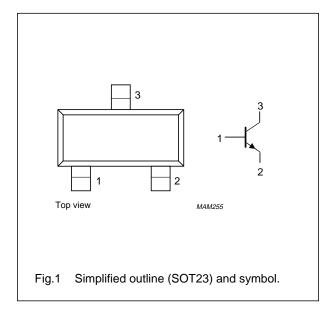
NPN transistor in a SOT23 plastic package. PNP complements: BC856, BC857 and BC858.

#### **MARKING**

TYPE NUMBER	MARKING CODE(1)
BC846	1D*
BC846A	1A*
BC846B	1B*
BC847	1H*
BC847A	1E*
BC847B	1F*
BC847C	1G*
BC848B	1K*

#### **PINNING**

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



#### Note

- 1. \* = p: made in Hong Kong.
  - \* = t: made in Malaysia.
  - \* = W: made in China.

#### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE			
	NAME	DESCRIPTION	VERSION	
BC846	-	plastic surface mounted package; 3 leads	SOT23	
BC846A				
BC846B				
BC847				
BC847A				
BC847B				
BC847C				
BC848B				

## NPN general purpose transistors

BC846; BC847; BC848

#### LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	BOL PARAMETER CONDITIONS		MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC846		_	80	V
	BC847		_	50	V
	BC848		_	30	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC846		_	65	V
	BC847		_	45	V
	BC848		_	30	V
V <sub>EBO</sub>	emitter-base voltage	open collector			
	BC846; BC847		_	6	V
	BC848		_	5	V
I <sub>C</sub>	collector current (DC) – 100		100	mA	
I <sub>CM</sub>	peak collector current – 200		200	mA	
I <sub>BM</sub>	peak base current – 200		200	mA	
P <sub>tot</sub>	total power dissipation T <sub>amb</sub> ≤ 25 °C; note 1 –		_	250	mW
T <sub>stg</sub>	storage temperature -65 +1		+150	°C	
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature -65 +150		°C		

#### Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air; note 1	500	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

## NPN general purpose transistors

BC846; BC847; BC848

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

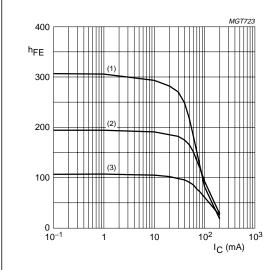
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0	_	-	15	nA
		$V_{CB} = 30 \text{ V; } I_{E} = 0;$ $T_{j} = 150 \text{ °C}$	_	_	5	μА
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	_	-	100	nA
h <sub>FE</sub>	DC current gain	$I_C = 10 \mu A; V_{CE} = 5 V$				
	BC846A; BC847A		_	90	_	
	BC846B; BC847B; BC848B		-	150	-	
	BC847C		_	270	_	
	DC current gain	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$				
	BC846		110	_	450	
	BC847		110	_	800	
	BC846A; BC847A		110	180	220	
	BC846B; BC847B; BC848B		200	290	450	
	BC847C		420	520	800	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	90	250	mV
		$I_C = 100 \text{ mA}; I_B = 5 \text{ mA};$ note 1	-	200	600	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	700	-	mV
		$I_C = 100 \text{ mA}; I_B = 5 \text{ mA};$ note 1	-	900	_	mV
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V	580	660	700	mV
		I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V	_	_	770	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = I_{e} = 0;$ f = 1 MHz	_	2.5	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
F	noise figure	$I_{C} = 200 \ \mu\text{A}; \ V_{CE} = 5 \ \text{V}; \\ R_{S} = 2 \ k\Omega; \ f = 1 \ \text{kHz}; \\ B = 200 \ \text{Hz}$	-	2	10	dB

#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

## NPN general purpose transistors

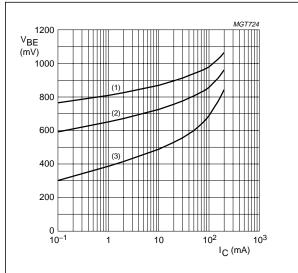
BC846; BC847; BC848



**BC846A**;  $V_{CE} = 5 \text{ V}$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

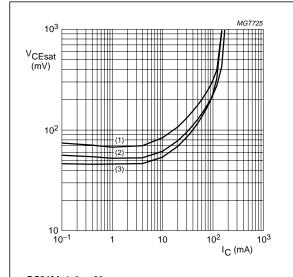
Fig.2 DC current gain as a function of collector current; typical values.



BC846A; V<sub>CE</sub> = 5 V.

- (1)  $T_{amb} = -55 \,^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

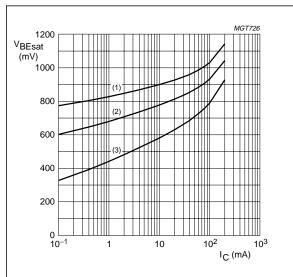
Fig.3 Base-emitter voltage as a function of collector current; typical values.



**BC846A**;  $I_C/I_B = 20$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



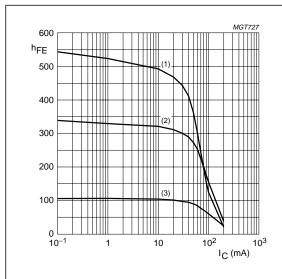
**BC846A**;  $I_C/I_B = 10$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

## NPN general purpose transistors

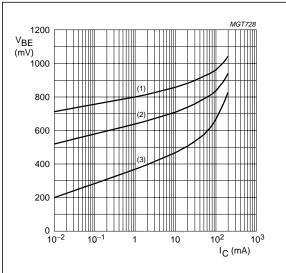
BC846; BC847; BC848



**BC847B**;  $V_{CE} = 5 \text{ V}$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

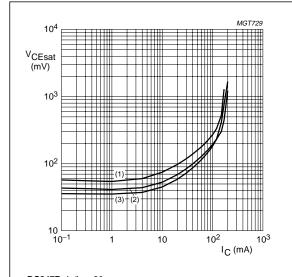
Fig.6 DC current gain as a function of collector current; typical values.



**BC847B**;  $V_{CE} = 5 \text{ V}$ .

- (1)  $T_{amb} = -55 \,^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

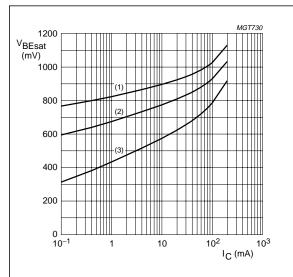
Fig.7 Base-emitter voltage as a function of collector current; typical values.



**BC847B**;  $I_C/I_B = 20$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



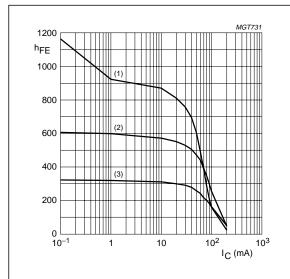
**BC847B**;  $I_{\rm C}/I_{\rm B} = 10$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

## NPN general purpose transistors

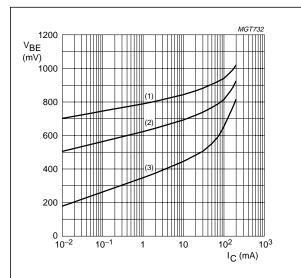
BC846; BC847; BC848



**BC847C**;  $V_{CE} = 5 \text{ V}$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

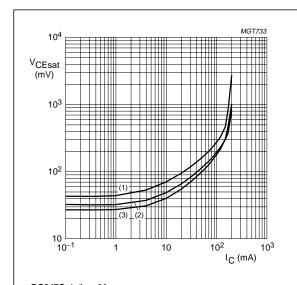
Fig.10 DC current gain as a function of collector current; typical values.



**BC847C**;  $V_{CE} = 5 \text{ V}$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

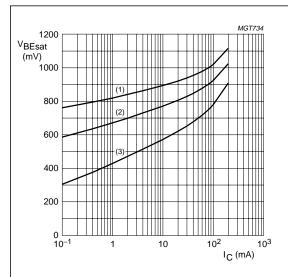
Fig.11 Base-emitter voltage as a function of collector current; typical values.



**BC847C**;  $I_C/I_B = 20$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



**BC847C**;  $I_C/I_B = 10$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

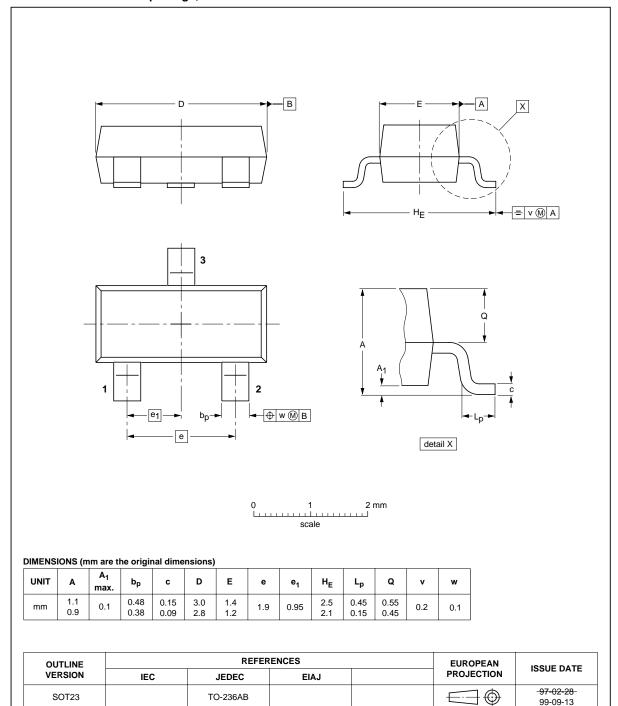
## NPN general purpose transistors

BC846; BC847; BC848

#### **PACKAGE OUTLINE**

#### Plastic surface mounted package; 3 leads

SOT23



### NPN general purpose transistors

BC846; BC847; BC848

#### **DATA SHEET STATUS**

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